Saluru B Krupanidhi

List of Publications by Year in Descending Order

419 papers	9,271 citations	47 h-index	74 g-index
444 ext. papers	10,062 ext. citations	2.7 avg, IF	6.4 L-index

#	Paper	IF	Citations
419	MoS2/SnO2 heterojunction-based self-powered photodetector. *Applied Physics Letters*, **2022**, 120, 181106	3.4	1
418	Inhomogeneity-mediated systematic reduction of the Schottky barrier in a Au/GaN nanorod film interface. *Semiconductor Science and Technology*, **2021**, 36, 015017	1.8	1
417	Solution-Processed SnSe2–rGO-Based Bulk Heterojunction for Self-Powered and Broadband Photodetection. *ACS Applied Electronic Materials*, **2021**, 3, 3131-3138	4	3
416	Electrical transport modulation of VO2/Si(111) heterojunction by engineering interfacial barrier height. *Journal of Applied Physics*, **2021**, 129, 244502	2.5	2
415	Infrared photodetectors based on multiwalled carbon nanotubes: Insights into the effect of nitrogen doping. *Applied Surface Science*, **2021**, 538, 148187	6.7	21
414	Enhanced phase transition and infrared photoresponse characteristics in VO2(M1) thin films synthesized by DC reactive sputtering on different substrates. *Materials Advances*, **2021**, 2, 3726-3735	3.3	0
413	Overcoming the Challenges Associated with the InN/InGaN Heterostructure via a Nanostructuring Approach for Broad Band Photodetection. *ACS Applied Electronic Materials*, **2021**, 3, 4243-4253	4	2
412	Differentiation of ultraviolet/visible photons from near infrared photons by MoS2/GaN/Si-based photodetector. *Applied Physics Letters*, **2021**, 119, 121102	3.4	6
411	Defect-Mediated Transport in Self-Powered, Broadband, and Ultrafast Photoresponse of a MoS2/AlN/Si-Based Photodetector. *ACS Applied Electronic Materials*, **2020**, 2, 944-953	4	21
410	Iron-Based Mixed Phosphate NaFe(PO)PO Thin Films for Sodium-Ion Microbatteries. *ACS Omega*, **2020**, 5, 7219-7224	3.9	8
409	Different types of band alignment at MoS2/(Al, Ga, In)N heterointerfaces. *Applied Physics Letters*, **2020**, 116, 252102	3.4	4
408	Highly Responsive, Self-Powered a-GaN Based UV-A Photodetectors Driven by Unintentional Asymmetrical Electrodes. *ACS Applied Electronic Materials*, **2020**, 2, 769-779	4	17
407	Next-generation self-powered and ultrafast photodetectors based on III-nitride hybrid structures. *APL Materials*, **2020**, 8, 020907	5.7	13
406	Highly photoresponsive VO2(M1) thin films synthesized by DC reactive sputtering. *Journal of Materials Science: Materials in Electronics*, **2020**, 31, 4687-4695	2.1	5
405	Fabrication of smooth thin film of vanadium oxides ((hbox {VO}_x)) using pulsed laser deposition. *Applied Physics A: Materials Science and Processing*, **2020**, 126, 1	2.6	5
404	Defect and strain modulated highly efficient ZnO UV detector: Temperature and low-pressure dependent studies. *Applied Surface Science*, **2020**, 505, 144365	6.7	27
403	Harvesting energy via stimuli-free water/moisture dissociation by mesoporous SnO2-based hydroelectric cell and CuO as a pump for atmospheric moisture. *International Journal of Energy Research*, **2020**, 44, 1276-1283	4.5	7

402	Temperature-Dependent Electrical Transport and Optoelectronic Properties of SnS2/p-Si Heterojunction. *ACS Applied Electronic Materials*, **2020**, 2, 2155-2163	4	10
401	Temperature Dependent S-Shaped Photoluminescence Behavior of InGaN Nanolayers: Optoelectronic Implications in Harsh Environment. *ACS Applied Nano Materials*, **2020**, 3, 8453-8460	5.6	3
400	Device Architecture for Visible and Near-Infrared Photodetectors Based on Two-Dimensional SnSe and MoS: A Review. *Micromachines*, **2020**, 11,	3.3	9
399	Self-powered, ultrasensitive, room temperature humidity sensors using SnS nanofilms. *Scientific Reports*, **2020**, 10, 14611	4.9	5
398	Enhanced humidity responsive ultrasonically nebulised V2O5 thin films. *Nano Express*, **2020**, 1, 010005	2	8
397	NO gas sensing performance enhancement based on reduced graphene oxide decorated VO thin films. *Nanotechnology*, **2019**, 30, 224001	3.4	15
396	Highly Responsive ZnO/AlN/Si Heterostructure-Based Infrared- and Visible-Blind Ultraviolet Photodetectors With High Rejection Ratio. *IEEE Transactions on Electron Devices*, **2019**, 66, 1345-1352	2.9	10
395	Photodetection Properties of Nonpolar a-Plane GaN Grown by Three Approaches Using Plasma-Assisted Molecular Beam Epitaxy. *Physica Status Solidi (A) Applications and Materials Science* , **2019**, 216, 1900171	1.6	10
394	A high-performance hydrogen sensor based on a reverse-biased MoS/GaN heterojunction. *Nanotechnology*, **2019**, 30, 314001	3.4	22
393	Low-cost VO(M1) thin films synthesized by ultrasonic nebulized spray pyrolysis of an aqueous combustion mixture for IR photodetection.. *RSC Advances*, **2019**, 9, 9983-9992	3.7	16
392	Self-Powered, Broad Band, and Ultrafast InGaN-Based Photodetector. *ACS Applied Materials & Interfaces*, **2019**, 11, 10418-10425	9.5	39
391	Double Gaussian distribution of barrier heights and self-powered infrared photoresponse of InN/AlN/Si (111) heterostructure. *Journal of Applied Physics*, **2019**, 126, 025301	2.5	13
390	Toward a Fast and Highly Responsive SnSe-Based Photodiode by Exploiting the Mobility of the Counter Semiconductor. *ACS Applied Materials & Interfaces*, **2019**, 11, 6184-6194	9.5	21
389	Preferentially oriented SrLi2Ti6O14 thin film anode for Li-ion micro-batteries fabricated by pulsed laser deposition. *Electrochimica Acta*, **2018**, 269, 212-216	6.7	4
388	Vis-Near-Infrared Photodetectors Based on Methyl Ammonium Lead Iodide Thin Films by Pulsed Laser Deposition. *Journal of Electronic Materials*, **2018**, 47, 2306-2315	1.9	4
387	In-Plane Anisotropic Photoconduction in Nonpolar Epitaxial a-Plane GaN. *ACS Applied Materials & Interfaces*, **2018**, 10, 16918-16923	9.5	22
386	Superior Electrochemical Performance of Amorphous Titanium Niobium Oxide Thin Films for Li-Ion Thin Film Batteries. *Journal of the Electrochemical Society*, **2018**, 165, A764-A772	3.9	10
385	Wafer-scale synthesis of a uniform film of few-layer MoS2 on GaN for 2D heterojunction ultraviolet photodetector. *Journal Physics D: Applied Physics*, **2018**, 51, 374003	3	30

384	An Extrinsic Approach Toward Achieving Fast Response and Self-Powered Photodetector. *Physica Status Solidi (A) Applications and Materials Science*, **2018**, 215, 1800470	1.6	14
383	An Overview of Nanostructured Li-based Thin Film Micro-batteries **2018**, 98,		4
382	Gallium and indium co-doped ZnO as a transparent conducting oxide for Cu2SnS3 photodetectors. *Journal of Materials Science: Materials in Electronics*, **2018**, 29, 2131-2139	2.1	5
381	BTO/GaN heterostructure based on Schottky junction for high-temperature selective ultra-violet photo detection. *Journal Physics D: Applied Physics*, **2018**, 51, 045104	3	8
380	In-situ deposition of sodium titanate thin film as anode for sodium-ion micro-batteries developed by pulsed laser deposition. *Journal of Colloid and Interface Science*, **2018**, 514, 117-121	9.3	10
379	Temperature dependent electrical properties of AlN/Si heterojunction. *Journal of Applied Physics*, **2018**, 124, 205111	2.5	5
378	Reduced graphene oxide-based broad band photodetector and temperature sensor: effect of gas adsorption on optoelectrical properties. *Journal of Nanoparticle Research*, **2018**, 20, 1	2.3	9
377	Heterostructures of III-Nitride Semiconductors for Optical and Electronic Applications **2018**,		2
376	Note: Simultaneous water quality monitoring and degradation of hazardous organic pollutants. *Review of Scientific Instruments*, **2018**, 89, 096102	1.7	4
375	Enhanced optical absorption of graphene-based heat mirror with tunable spectral selectivity. *Solar Energy Materials and Solar Cells*, **2018**, 186, 149-153	6.4	40
374	Solvothermal Synthesis of CuSnS Quantum Dots and Their Application in Near-Infrared Photodetectors. *Inorganic Chemistry*, **2017**, 56, 2198-2203	5.1	39
373	Heat-up synthesis of Cu2SnS3 quantum dots for near infrared photodetection. *RSC Advances*, **2017**, 7, 23301-23308	3.7	22
372	Polarization-induced interfacial coupling modulations in BaTiO3/GaN heterojunction devices. *Journal Physics D: Applied Physics*, **2017**, 50, 275101	3	7
371	Negative differential resistance and resistive switching in SnO2/ZnO interface. *Journal of Applied Physics*, **2017**, 122, 125303	2.5	6
370	Solution-Cast Photoconductive Photodetectors Based on CuInSe Nanoparticles. *Journal of Nanoscience and Nanotechnology*, **2017**, 17, 1538-542	1.3	2
369	Reduced graphene oxide film based highly responsive infrared detector. *Materials Research Express*, **2017**, 4, 085603	1.7	7
368	Quantum Phase Transition in Few-Layer NbSe_{2} Probed through Quantized Conductance Fluctuations. *Physical Review Letters*, **2017**, 119, 226802	7.4	11
367	Band Gap Engineering of Hexagonal SnSe Nanostructured Thin Films for Infra-Red Photodetection. *Scientific Reports*, **2017**, 7, 15215	4.9	74

366	Sequential Elemental Dealloying Approach for the Fabrication of Porous Metal Oxides and Chemiresistive Sensors Thereof for Electronic Listening. *ACS Applied Materials & Interfaces*, **2017**, 9, 41428-41434	9.5	18
365	Effect of Illumination Intensities on the Visible and Infrared Photoresponse of Cu$_3$SnS$_4$ Nanostructures. *Journal of Nanoscience and Nanotechnology*, **2017**, 17, 413-19	1.3	5
364	Mechanistic view on efficient photodetection by solvothermally reduced graphene oxide. *Journal of Materials Science: Materials in Electronics*, **2017**, 28, 14818-14826	2.1	8
363	Experimental evidence on RH-dependent crossover from an electronic to protonic conduction with an oscillatory behaviour. *Applied Physics Letters*, **2017**, 110, 263506	3.4	14
362	Na2Ti6O13 thin films as anode for thin film sodium ion batteries **2017**,		1
361	Enhanced UV Photodetector Response of ZnO/Si With AlN Buffer Layer. *IEEE Transactions on Electron Devices*, **2017**, 64, 4161-4166	2.9	17
360	Deep UV-Vis photodetector based on ferroelectric/semiconductor heterojunction. *Journal of Applied Physics*, **2017**, 122, 234502	2.5	13
359	Controlled growth of high-quality graphene using hot-filament chemical vapor deposition. *Applied Physics A: Materials Science and Processing*, **2016**, 122, 1	2.6	7
358	Understanding Pt/ZnO:In Schottky nanocontacts by conductive atomic force microscopy. *Materials Research Express*, **2016**, 3, 045023	1.7	4
357	Fabrication of TiNb2O7 thin film electrodes for Li-ion micro-batteries by pulsed laser deposition. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2016**, 213, 90-97	3.1	23
356	InN Quantum Dot Based Infra-Red Photodetectors. *Journal of Nanoscience and Nanotechnology*, **2016**, 16, 709-14	1.3	9
355	Structural and optical characterization of nonpolar (10$\bar{1}$0) m-InN/m-GaN epilayers grown by PAMBE. *Journal of Crystal Growth*, **2016**, 433, 74-79	1.6	5
354	Role of component layers in designing carbon nanotubes-based tandem absorber on metal substrates for solar thermal applications. *Solar Energy Materials and Solar Cells*, **2016**, 155, 397-404	6.4	6
353	Novel Radiation-Induced Properties of Graphene and Related Materials **2016**, 159-189		
352	Solution processed Cu2SnS3 thin films for visible and infrared photodetector applications. *AIP Advances*, **2016**, 6, 025217	1.5	38
351	Cu2SnS3nanostructures for inorganic/organic hybrid infrared photodetector applications. *Materials Research Express*, **2016**, 3, 105006	1.7	7
350	Transport properties of solution processed Cu2SnS3/AZnO heterostructure for low cost photovoltaics. *Solar Energy Materials and Solar Cells*, **2015**, 143, 152-158	6.4	32
349	Preferential polarization and its reversal in polycrystalline BiFeO3/La0.5Sr0.5CoO3 heterostructures. *Solid State Communications*, **2015**, 208, 15-20	1.6	3

348	Growth and electrical transport properties of InGaN/GaN heterostructures grown by PAMBE. *Materials Research Bulletin*, **2015**, 61, 539-543	5.1	7
347	High indium non-polar InGaN clusters with infrared sensitivity grown by PAMBE. *AIP Advances*, **2015**, 5, 037112	1.5	6
346	Binary group III-nitride based heterostructures: band offsets and transport properties. *Journal Physics D: Applied Physics*, **2015**, 48, 423001	3	40
345	Trap modulated photoresponse of InGaN/Si isotype heterojunction at zero-bias. *Journal of Applied Physics*, **2015**, 118, 024503	2.5	16
344	Barrier height inhomogeneity in electrical transport characteristics of InGaN/GaN heterostructure interfaces. *AIP Advances*, **2015**, 5, 037130	1.5	13
343	An insight to the low temperature conduction mechanism ofc-axis grown Al-doped ZnO, a widely used transparent conducting oxide. *Journal Physics D: Applied Physics*, **2015**, 48, 015301	3	9
342	CuIn1⊠AlxSe2 Thin Films Grown by Co-Sputtering and Modified Selenization: Application in Flexible Solar Cells. *IEEE Journal of the Electron Devices Society*, **2015**, 3, 244-253	2.3	2
341	Cu2SnS3 Inorganic-Organic Hybrid Structures for Photovoltaic Applications. *Materials Research Society Symposia Proceedings*, **2015**, 1784, 1		1
340	Determination of band offsets at the Al:ZnO/Cu2SnS3 interface using X-ray photoelectron spectroscopy. *AIP Advances*, **2015**, 5, 047137	1.5	6
339	Enhanced UV detection by non-polar epitaxial GaN films. *AIP Advances*, **2015**, 5, 127208	1.5	26
338	Temperature dependent electrical characterisation of Pt/HfO2/n-GaN metal-insulator-semiconductor (MIS) Schottky diodes. *AIP Advances*, **2015**, 5, 097103	1.5	36
337	Impact of Nitridation on Structural and Optical Properties of Epitaxial GaN Films Grown on M-Plane Sapphire by PAMBE. *Materials Research Society Symposia Proceedings*, **2015**, 1736, 76		1
336	Nanocomposite Based Organic-Inorganic Cu3BiS3 High Sensitive Hybrid Photonic Devices. *Journal of Nanoscience and Nanotechnology*, **2015**, 15, 2742-52	1.3	6
335	Study of band offsets at the Cu2SnS3/In2O3: Sn interface using x-ray photoelectron spectroscopy. *Materials Research Express*, **2015**, 2, 065901	1.7	4
334	Solution processible Cu 2 SnS 3 thin films for cost effective photovoltaics: Characterization. *Materials Chemistry and Physics*, **2015**, 167, 309-314	4.4	19
333	Observation of Room Temperature Ferromagnetism in InN Nanostructures. *Journal of Nanoscience and Nanotechnology*, **2015**, 15, 4426-30	1.3	7
332	Temperature dependent electrical behaviour of Cu2SnS3 films. *AIP Advances*, **2014**, 4, 037121	1.5	10
331	Transport properties of CuIn(1-x)Al(x)Se2/AZnO heterostructure for low cost thin film photovoltaics. *Dalton Transactions*, **2014**, 43, 1974-83	4.3	28

330	Effects of growth temperature on nonpolar a-plane InN grown by molecular beam epitaxy. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2014**, 11, 932-935		3
329	Fabrication of large-area PbSe films at the organic□queous interface and their near-infrared photoresponse. *Journal of Materials Chemistry C*, **2014**, 2, 6283	7.1	8
328	Carbon nanotube-based tandem absorber with tunable spectral selectivity: transition from near-perfect blackbody absorber to solar selective absorber. *Advanced Materials*, **2014**, 26, 2552-7	24	71
327	Solution Processed Cu2CoSnS4 Thin Films for Photovoltaic Applications. *Crystal Growth and Design*, **2014**, 14, 3685-3691	3.5	49
326	Double Gaussian distribution of barrier height observed in densely packed GaN nanorods over Si (111) heterostructures. *Journal of Applied Physics*, **2014**, 116, 234508	2.5	6
325	Plasmonic enhancement of photocurrent in GaN based UV photodetectors **2014**,		7
324	Semipolar and nonpolar GaN epi-films grown on m-sapphire by plasma assisted molecular beam epitaxy. *Journal of Applied Physics*, **2014**, 116, 204502	2.5	31
323	Near-infrared photoactive Cu3BiS3 thin films by co-evaporation. *Journal of Applied Physics*, **2014**, 115, 173109	2.5	22
322	Growth and Characterization of a-plane In0.2Ga0.8N/ GaN hetrostructures on r-Sapphire. *Materials Research Society Symposia Proceedings*, **2014**, 1736, 31		
321	Pt/n-GaN metal-semiconductor and Pt/HfO2/n-GaN metal-insulator-semiconductor Schottky diodes. *Materials Research Society Symposia Proceedings*, **2014**, 1736, 7		
320	Smart Materials for Energy Harvesting, Energy Storage, and Energy Efficient Solid-State Electronic Refrigeration. *Springer Tracts in Mechanical Engineering*, **2014**, 303-315	0.3	1
319	Study of InN nanorods growth mechanism using ultrathin Au layer by plasma-assisted MBE on Si(111). *Applied Nanoscience (Switzerland)*, **2014**, 4, 121-125	3.3	2
318	Impact of substrate nitridation on the photoluminescence and photovoltaic characteristics of GaN grown on p-Si (100) by molecular beam epitaxy. *Journal of Materials Science: Materials in Electronics*, **2013**, 24, 3371-3375	2.1	1
317	Anomalous magnetic behavior of La0.6Sr0.4MnO3 nano-tubes constituted with 3□2 nm particles. *Applied Physics A: Materials Science and Processing*, **2013**, 111, 605-612	2.6	14
316	Facile synthesis of Cu2CoSnS4 nanoparticles exhibiting red-edge-effect: Application in hybrid photonic devices. *Journal of Applied Physics*, **2013**, 114, 144312	2.5	49
315	Near infrared detectors based on HgSe and HgCdSe quantum dots generated at the liquid□quid interface. *Journal of Materials Chemistry C*, **2013**, 1, 6184	7.1	31
314	Substrate impact on the growth of InN nanostructures by droplet epitaxy. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2013**, 10, 409-412		4
313	Low dimensional fabrication of giant dielectric CaCu3Ti4O12 through soft e-beam lithography. *Journal of Alloys and Compounds*, **2013**, 547, 147-151	5.7	12

312	Electrical transport studies of MBE grown InGaN/Si isotype heterojunctions. *Current Applied Physics* , **2013**, 13, 26-30	2.6	12
311	Spectroscopic studies of In2O3 nanostructures; photovoltaic demonstration of In2O3/p-Si heterojunction. *Journal of Nanoscience and Nanotechnology*, **2013**, 13, 498-503	1.3	4
310	Sol-gel processed Cu2SnS3 films for photovoltaics **2013**,		1
309	Electrical and Optical Properties of Electron Irradiated ZnO: Li Thin Films. *Advanced Materials Research*, **2013**, 699, 257-261	0.5	1
308	Molecular beam epitaxial growth of (1 1 -2 2) GaN on m-plane sapphire. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2013**, 10, 381-384		1
307	Electrocaloric Effect in 0.85PMN-0.15PT Thin Films Deposited by Pulsed Laser Deposition. *Ferroelectrics*, **2013**, 453, 38-43	0.6	3
306	Near-infrared photoactive Cu2ZnSnS4 thin films by co-sputtering. *AIP Advances*, **2013**, 3, 082132	1.5	26
305	Tailoring the Cu(In, Al)S2 nanostructures for photonic applications **2013**,		3
304	Tailoring the band gap and transport properties of Cu3BiS3 nanopowders for photodetector applications. *Journal of Nanoscience and Nanotechnology*, **2013**, 13, 3901-9	1.3	12
303	Carrier concentration dependence of donor activation energy in n-type GaN epilayers grown on Si (111) by plasma-assisted MBE. *Materials Research Bulletin*, **2012**, 47, 1306-1309	5.1	11
302	Valence band offset at GaN/Si3N4 and Si3N4/Si(111) heterojunctions formed by plasma-assisted molecular beam epitaxy. *Thin Solid Films*, **2012**, 520, 4911-4915	2.2	12
301	Study of n-ZnO/p-Si (100) thin film heterojunctions by pulsed laser deposition without buffer layer. *Thin Solid Films*, **2012**, 520, 5894-5899	2.2	59
300	Solution-based synthesis of cobalt-doped ZnO thin films. *Thin Solid Films*, **2012**, 524, 137-143	2.2	37
299	Effect of carrier concentration of InN on the transport behavior of InN/GaN heterostructure based Schottky junctions. *Solid State Communications*, **2012**, 152, 1771-1775	1.6	2
298	Indium flux, growth temperature and RF power induced effects in InN layers grown on GaN/Si substrate by plasma-assisted MBE. *Journal of Alloys and Compounds*, **2012**, 513, 6-9	5.7	8
297	Cobalt-doped ZnO nanowires on quartz: Synthesis by simple chemical method and characterization. *Journal of Crystal Growth*, **2012**, 343, 7-12	1.6	27
296	Influence of GaN underlayer thickness on structural, electrical and optical properties of InN films grown by PAMBE. *Journal of Crystal Growth*, **2012**, 354, 208-211	1.6	10
295	Large nonlinear refraction and two photon absorption in ferroelectric Bi2VO5.5 thin films. *Optical Materials*, **2012**, 34, 1822-1825	3.3	7

294	Synthesis and structural characterization of two-dimensional hierarchical covellite nano-structures. *Materials Chemistry and Physics*, **2012**, 137, 466-471	4.4	16
293	Perovskite phase transformation in 0.65Pb(Mg1/3Nb2/3)O3-0.35PbTiO3 nanoparticles derived by sol-gel. *Journal of Applied Physics*, **2012**, 111, 024314	2.5	4
292	Gallium and indium co-doped ZnO thin films for white light emitting diodes. *Physica Status Solidi - Rapid Research Letters*, **2012**, 6, 34-36	2.5	18
291	Determination of MBE grown wurtzite GaN/Ge3N4/Ge heterojunctions band offset by X-ray photoelectron spectroscopy. *Physica Status Solidi (B): Basic Research*, **2012**, 249, 58-61	1.3	15
290	Carrier-transport studies of III-nitride/Si3N4/Si isotype heterojunctions. *Physica Status Solidi (A) Applications and Materials Science*, **2012**, 209, 994-997	1.6	9
289	Analysis of the temperature-dependent current□oltage characteristics and the barrier-height inhomogeneities of Au/GaN Schottky diodes. *Physica Status Solidi (A) Applications and Materials Science*, **2012**, 209, 1575-1578	1.6	9
288	Novel Radiation-Induced Properties of Graphene and Related Materials. *Macromolecular Chemistry and Physics*, **2012**, 213, 1146-1163	2.6	63
287	Comparative studies on photovoltaic performance of InN nanostructures/p-Si(100) heterojunction devices grown by molecular beam epitaxy. *Materials Research Society Symposia Proceedings*, **2012**, 1391, 95		1
286	Current transport in nonpolar a-plane InN/GaN heterostructures Schottky junction. *Journal of Applied Physics*, **2012**, 112, 023706	2.5	14
285	Unusual photoresponse of indium doped ZnO/organic thin film heterojunction. *Applied Physics Letters*, **2012**, 100, 162104	3.4	56
284	Structural Characterization and Ultraviolet Photoresponse of GaN Nanodots Grown by Molecular Beam Epitaxy. *Applied Physics Express*, **2012**, 5, 085202	2.4	9
283	Studies on Field Dependent Domain Structures in Multi-Grained 0.85PbMg1/3Nb2/3O3□0.15PbTiO3 Thin Films by Scanning Force Microscopy. *Integrated Ferroelectrics*, **2012**, 134, 39-47	0.8	1
282	Band-Structure Lineup at In$_{0.2}$Ga$_{0.8}$N/Si Heterostructures by X-ray Photoelectron Spectroscopy. *Japanese Journal of Applied Physics*, **2012**, 51, 020203	1.4	2
281	Solvothermal Synthesis, Structural and Optical Properties of Phase-Pure Cu3BiS3 Nano-Powders Exhibiting Near-IR Photodetection. *Advanced Science, Engineering and Medicine*, **2012**, 4, 89-95	0.6	3
280	Band-Structure Lineup at In0.2Ga0.8N/Si Heterostructures by X-ray Photoelectron Spectroscopy. *Japanese Journal of Applied Physics*, **2012**, 51, 020203	1.4	1
279	Substrate nitridation induced modulations in transport properties of wurtzite GaN/p-Si (100) heterojunctions grown by molecular beam epitaxy. *Journal of Applied Physics*, **2011**, 110, 093718	2.5	20
278	Experimental evidence of Ga-vacancy induced room temperature ferromagnetic behavior in GaN films. *Applied Physics Letters*, **2011**, 99, 162512	3.4	40
277	Size dependent bandgap of molecular beam epitaxy grown InN quantum dots measured by scanning tunneling spectroscopy. *Journal of Applied Physics*, **2011**, 110, 114317	2.5	8

276	An aqueous-solution based low-temperature pathway to synthesize giant dielectric CaCu3Ti4O12 highly porous ceramic matrix and submicron sized powder. *Journal of Alloys and Compounds*, **2011**, 509, 4381-4385	5.7	19
275	Structural and dielectric behavior of pulsed laser ablated Sr0.6Ca0.4TiO3 thin film and asymmetric multilayer of SrTiO3 and CaTiO3. *Journal of Crystal Growth*, **2011**, 337, 7-12	1.6	1
274	Effect of N/Ga flux ratio on transport behavior of Pt/GaN Schottky diodes. *Journal of Applied Physics*, **2011**, 110, 064502	2.5	8
273	Barrier height inhomogeneities in InN/GaN heterostructure based Schottky junctions. *Solid State Communications*, **2011**, 151, 1420-1423	1.6	14
272	Structural and optical properties of nonpolar (1 1 2 0) a-plane GaN grown on (1 1 0 2) r-plane sapphire substrate by plasma-assisted molecular beam epitaxy. *Scripta Materialia*, **2011**, 65, 33-36	5.6	15
271	Synthesis, structural characterization and ferroelectric properties of Pb0.76Ca0.24TiO3 nanotubes. *Materials Chemistry and Physics*, **2011**, 131, 443-448	4.4	5
270	Growth of InN layers on Si (111) using ultra thin silicon nitride buffer layer by NPA-MBE. *Materials Letters*, **2011**, 65, 1396-1399	3.3	18
269	Structural and electrical studies on Bi2VO5.5/Bi4Ti3O12 multilayer thin films. *Journal of Materials Science: Materials in Electronics*, **2011**, 22, 639-648	2.1	2
268	Kinetics of self-assembled InN quantum dots grown on Si (111) by plasma-assisted MBE. *Journal of Nanoparticle Research*, **2011**, 13, 1281-1287	2.3	11
267	Reduction of oxygen impurity at GaN/Si3N4/Si interface via SiO2 to Ga2O conversion by exposing of Si surface under Ga flux. *Journal of Crystal Growth*, **2011**, 327, 272-275	1.6	4
266	Synthesis and structural characterization of perovskite 0.65Pb(Mg1/3Nb2/3)O3 0.35PbTiO3 nanotubes. *Physics Letters, Section A: General, Atomic and Solid State Physics*, **2011**, 375, 2176-2180	2.3	5
265	Transport and infrared photoresponse properties of InN nanorods/Si heterojunction. *Nanoscale Research Letters*, **2011**, 6, 609	5	21
264	Evidences for ambient oxidation of indium nitride quantum dots. *Physica Status Solidi (B): Basic Research*, **2011**, 248, 2853-2856	1.3	4
263	Infrared photodetectors based on reduced graphene oxide and graphene nanoribbons. *Advanced Materials*, **2011**, 23, 5419-24	24	256
262	Solution processed reduced graphene oxide ultraviolet detector. *Applied Physics Letters*, **2011**, 99, 113114	3.4	92
261	The impact of ultra thin silicon nitride buffer layer on GaN growth on Si (1 1 1) by RF-MBE. *Applied Surface Science*, **2011**, 257, 2107-2110	6.7	8
260	Multilayer Bi1.5Zn1.0Nb1.5O7/Ba0.6Sr0.4TiO3/Bi1.5Zn1.0Nb1.5O7 thin films for tunable microwave applications. *Applied Surface Science*, **2011**, 257, 2214-2217	6.7	14
259	Temperature-dependent photoluminescence of GaN grown on Si3N4/Si (111) by plasma-assisted MBE. *Journal of Luminescence*, **2011**, 131, 614-619	3.8	10

258	Pulsed laser deposited ZnO/ZnO:Li multilayer for blue light emitting diodes. *Journal of Luminescence*, **2011**, 131, 1649-1654	3.8	9
257	Electroluminescence from GaN□olymer heterojunction. *Journal of Luminescence*, **2011**, 131, 2612-2615	3.8	4
256	Growth temperature induced effects in non-polar a-plane GaN on r-plane sapphire substrate by RF-MBE. *Journal of Crystal Growth*, **2011**, 314, 5-8	1.6	14
255	Negative differential capacitance in n-GaN/p-Si heterojunctions. *Solid State Communications*, **2011**, 151, 356-359	1.6	10
254	Study of band offsets in InN/Ge heterojunctions. *Surface Science*, **2011**, 605, L33-L37	1.8	3
253	Pulsed laser deposited ZnO:In as transparent conducting oxide. *Thin Solid Films*, **2011**, 519, 3647-3652	2.2	16
252	Effect of oxygen pressure on the grain and domain structure of polycrystalline 0.85PbMg1/3Nb2/3O3□0.15PbTiO3thin films studied by scanning probe microscopy. *Journal Physics D: Applied Physics*, **2011**, 44, 415401	3	3
251	Band alignment studies in InN/p-Si(100) heterojunctions by x-ray photoelectron spectroscopy. *Journal of Applied Physics*, **2011**, 109, 123707	2.5	15
250	Temperature dependent transport studies in InN quantum dots grown by droplet epitaxy on silicon nitride/Si substrate. *Applied Physics Letters*, **2011**, 99, 153114	3.4	12
249	Temperature dependent electrical transport behavior of InN/GaN heterostructure based Schottky diodes. *Journal of Applied Physics*, **2011**, 109, 044502-044502-5	2.5	22
248	Barrier Inhomogeneity and Electrical Properties of InN Nanodots/Si Heterojunction Diodes. *Journal of Nanomaterials*, **2011**, 2011, 1-7	3.2	4
247	Temperature dependent transport behavior of n-InN nanodot/p-Si heterojunction structures. *Applied Physics Letters*, **2010**, 97, 202107	3.4	16
246	Wide Ranged La Modification in CCTO Ceramics Through Sol-Gel: Effect on Microstructure and Dielectric Properties. *Integrated Ferroelectrics*, **2010**, 121, 86-98	0.8	2
245	High-temperature dielectric response in pulsed laser deposited Bi1.5Zn1.0Nb1.5O7 thin films. *Journal of Applied Physics*, **2010**, 108, 054106	2.5	10
244	Low Temperature Synthesis of Nano-Crystalline CaCu3Ti4O12 Through a Fuel Mediated Auto-Combustion Pathway. *Current Nanoscience*, **2010**, 6, 432-438	1.4	9
243	Facile hydrothermal synthesis and observation of bubbled growth mechanism in nano-ribbons aggregated microspherical Covellite blue-phosphor. *Dalton Transactions*, **2010**, 39, 9789-93	4.3	35
242	Polarization enhancement in compositionally graded vanadium doped bismuth titanate thin films. *Journal of Applied Physics*, **2010**, 107, 124105	2.5	8
241	Dielectric properties of electron irradiated PbZrO3 thin films. *Bulletin of Materials Science*, **2010**, 33, 191-196	1.1	5

240	Self-assembled flower-like nanostructures of InN and GaN grown by plasma-assisted molecular beam epitaxy. *Bulletin of Materials Science*, **2010**, 33, 221-226	1.7	14
239	Structural, optical and electrical characteristics of transparent bismuth vanadate films deposited on indium tin oxide coated glass substrates. *Journal of Materials Science: Materials in Electronics*, **2010**, 21, 1107-1114	2.1	5
238	ZnO nanocrystalline thin films: a correlation of microstructural, optoelectronic properties. *Journal of Materials Science: Materials in Electronics*, **2010**, 21, 355-359	2.1	18
237	Spectroscopic ellipsometry investigations of the optical properties of manganese doped bismuth vanadate thin films. *Materials Research Bulletin*, **2010**, 45, 464-473	5.1	5
236	Improved growth of GaN layers on ultra thin silicon nitride/Si (111) by RF-MBE. *Materials Research Bulletin*, **2010**, 45, 1581-1585	5.1	24
235	Impedance studies on high energy Li3+ irradiated PZT thin films. *Nuclear Instruments & Methods in Physics Research B*, **2010**, 268, 476-480	1.2	
234	Investigation of true remnant polarization response in heterostructured artificial biferroics. *Solid State Communications*, **2010**, 150, 660-662	1.6	8
233	Characteristics of field-effect transistors based on undoped and B- and N-doped few-layer graphenes. *Solid State Communications*, **2010**, 150, 734-738	1.6	58
232	Effect of La modification on antiferroelectricity and dielectric phase transition in sol□gel grown thin films. *Solid State Communications*, **2010**, 150, 1755-1759	1.6	9
231	Room-temperature gas sensors based on gallium nitride nanoparticles. *Solid State Communications*, **2010**, 150, 2053-2056	1.6	45
230	Probing disorder in cubic pyrochlore Bi1.5Zn1.0Nb1.5O7 (BZN) thin films. *Solid State Communications*, **2010**, 150, 2257-2261	1.6	6
229	Droplet Epitaxy of InN Quantum Dots on Si(111) by RF Plasma-Assisted Molecular Beam Epitaxy. *Advanced Science Letters*, **2010**, 3, 379-384	0.1	13
228	Structural and electrical characterization of Bi2VO5.5 / Bi4Ti3O12 bilayer thin films deposited by pulsed laser ablation technique. *Natural Science*, **2010**, 02, 1073-1078	0.5	1
227	Investigation of biferroic properties in La0.6Sr0.4MnO3/0.7Pb(Mg1/3Nb2/3)O3□0.3PbTiO3 epitaxial bilayered heterostructures. *Journal of Applied Physics*, **2009**, 106, 054103	2.5	10
226	Synthesis, structural characterization and formation mechanism of ferroelectric bismuth vanadate nanotubes. *Journal of Nanoscience and Nanotechnology*, **2009**, 9, 6549-53	1.3	6
225	Electrocaloric effect of PMN-PT thin films near morphotropic phase boundary. *Bulletin of Materials Science*, **2009**, 32, 259-262	1.7	109
224	Assembly of sol□gel-grown Li x CoO2 nanocrystals through electromagnetic irradiation. *Applied Physics A: Materials Science and Processing*, **2009**, 95, 523-536	2.6	1
223	Negative differential resistance in GaN nanocrystals above room temperature. *Nanotechnology*, **2009**, 20, 405205	3.4	14

222	Sol-Gel Template Synthesis, Structural Characterization and Growth Mechanism of Barium Zirconate Nanotubes. *Current Nanoscience*, **2009**, 5, 339-343	1.4	7
221	Synthesis of one-dimensional ZnO nanostructures from Zn powder/granule. *Journal of Nanoscience and Nanotechnology*, **2009**, 9, 2061-5	1.3	2
220	Fabrication and Phase Transformation in Crystalline Nanoparticles of PbZrO3 Derived By Sol-Gel. *Current Nanoscience*, **2009**, 5, 489-492	1.4	2
219	Surface spin glass behavior in sol-gel derived La0.7Ca0.3MnO3 nanotubes. *Dalton Transactions*, **2008**, 4708-10	4.3	10
218	Dielectric response of BaZrO3/BaTiO3 and SrTiO3/BaZrO3 superlattices. *Journal of Applied Physics*, **2008**, 104, 114105	2.5	17
217	Enhancement of charge and energy storage in sol-gel derived pure and La-modified PbZrO3 thin films. *Applied Physics Letters*, **2008**, 92, 192901	3.4	116
216	Constrained ferroelectricity in BaTiO3/BaZrO3 superlattices. *Applied Physics Letters*, **2008**, 92, 102903	3.4	14
215	dc leakage mechanism in artificial biferroic superlattices. *Journal of Applied Physics*, **2008**, 104, 104102	2.5	5
214	Slim P-E hysteresis loop and anomalous dielectric response in sol-gel derived antiferroelectric PbZrO3 thin films. *Journal of Applied Physics*, **2008**, 104, 024107	2.5	7
213	Lead zirconate nanotubes: synthesis, structural characterization and growth mechanism. *Journal of Nanoscience and Nanotechnology*, **2008**, 8, 5757-61	1.3	3
212	Structural, ferroelectric and optical properties of Bi2VO5.5 thin films deposited on platinized silicon {(100) Pt/TiO2/SiO2/Si} substrates. *Applied Physics A: Materials Science and Processing*, **2008**, 91, 693-699	2.6	13
211	Structural, optical and ac conduction properties of Bi2V1−xNbxO5.5 (0≤x≤0.4) thin films fabricated by pulsed laser deposition technique. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2008**, 153, 36-46	3.1	8
210	Magnetocapacitive La0.6Sr0.4MnO3 /0.7Pb(Mg1 / 3Nb2 / 3)O3−0.3PbTiO3 epitaxial heterostructure. *Solid State Communications*, **2008**, 148, 566-569	1.6	7
209	The structural and electrical properties of TiO2 thin films prepared by thermal oxidation. *Physica B: Condensed Matter*, **2008**, 403, 3718-3723	2.8	39
208	Electrocaloric effect in antiferroelectric PbZrO3 thin films. *Physica Status Solidi - Rapid Research Letters*, **2008**, 2, 230-232	2.5	52
207	Fabrication, Structural Characterization and Formation Mechanism of Multiferroic BiFeO3 Nanotubes. *Journal of Nanoscience and Nanotechnology*, **2008**, 8, 335-339	1.3	17
206	Studies on strontium titanate/barium zirconate superlattices. *Solid State Communications*, **2007**, 143, 223-227	1.6	1
205	Study of three-component ferroelectric perovskite superlattices. *Solid State Communications*, **2007**, 143, 510-514	1.6	4

204	Investigations on zinc oxide thin films grown on Si (1 0 0) by thermal oxidation. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2007**, 137, 126-130	3.1	13
203	Dielectric, impedance and ferroelectric characteristics of c-oriented bismuth vanadate films grown by pulsed laser deposition. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2007**, 138, 22-30	3.1	32
202	ac conductivity studies on the electron irradiated BaZrO3 ceramic. *Nuclear Instruments & Methods in Physics Research B*, **2007**, 257, 505-509	1.2	17
201	High energy oxygen ion induced modifications in lead based perovskite thin films. *Nuclear Instruments & Methods in Physics Research B*, **2007**, 260, 553-562	1.2	3
200	Investigations on magnetron sputtered ZnO thin films and Au/ZnO Schottky diodes. *Physica B: Condensed Matter*, **2007**, 391, 344-349	2.8	33
199	Synthesis and structural characterization of Ba0.6Sr0.4TiO3 nanotubes. *Physics Letters, Section A: General, Atomic and Solid State Physics*, **2007**, 367, 356-359	2.3	23
198	Synthesis and structural characterization of the antiferroelectric lead zirconate nanotubes by pulsed laser deposition. *Applied Physics A: Materials Science and Processing*, **2007**, 87, 27-30	2.6	11
197	Dielectric anomaly in Li-doped zinc oxide thin films grown by sol–gel route. *Applied Physics A: Materials Science and Processing*, **2007**, 88, 421-424	2.6	18
196	Off-centered polarization and ferroelectric phase transition in Li-doped ZnO thin films grown by pulsed-laser ablation. *Journal of Applied Physics*, **2007**, 101, 104104	2.5	43
195	Antiferroelectriclike polarization behavior in compositionally varying (1−x) Pb(Mg1/3Nb2/3)O3–(x) PbTiO3 multilayers. *Applied Physics Letters*, **2007**, 91, 082907	3.4	12
194	Role of template layer on microstructure, phase formation and polarization behavior of ferroelectric relaxor thin films. *Journal of Applied Physics*, **2007**, 101, 104111	2.5	5
193	Ferroelectric interaction and polarization studies in BaTiO3–SrTiO3 superlattice. *Journal of Applied Physics*, **2007**, 101, 104113	2.5	16
192	Leakage current behavior in pulsed laser deposited Ba(Zr0.05Ti0.95)O3 thin films. *Journal of Applied Physics*, **2007**, 101, 034106	2.5	37
191	Realization of biferroic properties in La0.6Sr0.4MnO3–0.7Pb(Mg1/3Nb2/3)O3–0.3(PbTiO3) epitaxial superlattices. *Journal of Applied Physics*, **2007**, 101, 114104	2.5	10
190	Improved ferroelectric and leakage properties in symmetric BiFeO3–SrTiO3 superlattice. *Applied Physics Letters*, **2007**, 90, 212902	3.4	33
189	Engineered Biferroic 0.7Pb(Mg1/3Nb2/3)O3-0.3PbTiO3/La0.6Sr0.4MnO3 Epitaxial Superlattices. *Materials Research Society Symposia Proceedings*, **2007**, 1034, 50		
188	Interface dominated biferroic La0.6Sr0.4MnO3–0.7Pb(Mg1/3Nb2/3)O3–0.3PbTiO3 epitaxial superlattices. *Applied Physics Letters*, **2007**, 90, 122902	3.4	37
187	Low threshold voltage ZnO thin film transistor with a Zn0.7Mg0.3O gate dielectric for transparent electronics. *Journal of Applied Physics*, **2007**, 101, 123717	2.5	40

186	Nonlinear dielectric behavior in three-component ferroelectric superlattices. *Journal of Applied Physics*, **2007**, 102, 024108	2.5	7
185	Dielectric properties of (110) oriented PbZrO3 and La-modified PbZrO3 thin films grown by sol-gel process on Pt(111)□Ti□SiO2□Si substrate. *Journal of Applied Physics*, **2006**, 100, 044102	2.5	27
184	Effect of Li substitution on dielectric and ferroelectric properties of ZnO thin films grown by pulsed-laser ablation. *Journal of Applied Physics*, **2006**, 99, 034105	2.5	43
183	Dielectric properties of c-axis oriented Zn1□MgxO thin films grown by multimagnetron sputtering. *Applied Physics Letters*, **2006**, 89, 082905	3.4	40
182	EFFECT OF MANGANESE DOPING ON THE ELECTRICAL CHARACTERISTICS OF SOL-GEL DERIVED LEAD ZIRCONATE TITANATE THIN FILMS. *Integrated Ferroelectrics*, **2006**, 82, 65-80	0.8	3
181	Growth of ferroelectric Li-doped ZnO thin films for metal-ferroelectric-semiconductor FET. *Journal Physics D: Applied Physics*, **2006**, 39, 2664-2669	3	25
180	Interfacial coupling and its size dependence in PbTiO3 and PbMg1□Nb2□O3 multilayers. *Physical Review B*, **2006**, 74,	3.3	29
179	Growth and transport properties of CuInSe2/ZnO heterostructure solar cell. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2006**, 127, 12-16	3.1	12
178	dc and ac transport properties of Mn-doped ZnO thin films grown by pulsed laser ablation. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2006**, 133, 70-76	3.1	33
177	Temperature dependent transport properties of CuInSe2□ZnO heterostructure solar Cell. *Journal of Physics and Chemistry of Solids*, **2006**, 67, 1636-1642	3.9	6
176	C□V studies on metal□ferroelectric bismuth vanadate (Bi2VO5.5)□semiconductor structure. *Solid State Communications*, **2006**, 137, 566-569	1.6	17
175	Ferroelectricity in Bi26□MxO40□(M=Al and Ga) with the □Bi2O3 structure. *Solid State Communications*, **2006**, 140, 42-44	1.6	11
174	Impact of microstructure on electrical characteristics of laser ablation grown ZrTiO4thin films on Si substrate. *Journal Physics D: Applied Physics*, **2005**, 38, 41-50	3	15
173	AC properties of laser ablated La-modified lead titanate thin films. *Thin Solid Films*, **2005**, 474, 1-9	2.2	40
172	Enhanced ferroelectric properties of vanadium doped bismuth titanate (BTV) thin films grown by pulsed laser ablation technique. *Solid State Communications*, **2005**, 133, 611-614	1.6	12
171	Deep level transient spectroscopy studies on BaTiO3and Ba1□CaxTiO3thin films deposited on Si substrates. *Semiconductor Science and Technology*, **2005**, 20, 250-255	1.8	4
170	dc leakage behavior in vanadium-doped bismuth titanate thin films. *Journal of Applied Physics*, **2005**, 98, 094112	2.5	33
169	Dielectric phase-transition and polarization studies in stepped and compositionally graded lead magnesium niobate□lead titanate relaxor thin films. *Journal of Applied Physics*, **2005**, 98, 014105	2.5	8

168	High Energy Oxygen Ion Induced Modifications in Ferroelectric SrBi2Ta2O9 Thin Films. *Ferroelectrics*, **2005**, 328, 103-109	0.6	3
167	Enhanced tunability and phase transition studies in compositionally varying lead magnesium niobate□lead titanate multilayered thin films. *Applied Physics Letters*, **2005**, 86, 092902	3.4	13
166	Biferroic YCrO3. *Physical Review B*, **2005**, 72,	3.3	178
165	Investigation of Relaxor Behavior in Pb(Mgg1/3Nb2/3)O3-PbTiO3 Thin Films. *Ferroelectrics*, **2004**, 306, 17-27	0.6	1
164	Impact of microstructure on dielectric properties of Pb(Mg1/3Nb2/3)O3□PbTiO3 thin films. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2004**, 106, 111-119	3.1	11
163	Effect of electric field on dielectric response of PMN□PT thin films **2004**, 113, 190-190		4
162	Electrical properties of ferroelectric YMnO3films deposited on n-type Si(111) substrates. *Journal Physics D: Applied Physics*, **2003**, 36, 2134-2140	3	13
161	Dielectric relaxation in laser ablated polycrystalline ZrTiO4 thin films. *Journal of Applied Physics*, **2003**, 94, 5135	2.5	49
160	Relaxor type perovskites: Primary candidates of nano-polar regions. *Journal of Chemical Sciences*, **2003**, 115, 775-788	1.8	9
159	Study of La-modified antiferroelectric PbZrO3 thin films. *Thin Solid Films*, **2003**, 423, 88-96	2.2	18
158	High energy Li ion irradiation effects in ferroelectric PZT and SBT thin films. *Thin Solid Films*, **2003**, 434, 40-48	2.2	18
157	Structural and optical properties of CuIn1□AlxSe2 thin films prepared by four-source elemental evaporation. *Solid State Communications*, **2003**, 127, 243-246	1.6	23
156	Study of relaxor-like behaviour of laser ablated (Pb, La)Tio3 thin films. *Solid State Communications*, **2003**, 127, 247-251	1.6	8
155	Dielectric response and impedance spectroscopy of 0.7Pb(Mg1/3Nb2/3)O3□.3PbTiO3 thin films. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2003**, 98, 204-212	3.1	31
154	Ac conductivity studies on the Li irradiated PZT and SBT ferroelectric thin films. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2003**, 100, 93-101	3.1	28
153	Role of La0.5Sr0.5CoO3 template layers on dielectric and electrical properties of pulsed-laser ablated Pb(Nb2/3Mg1/3)O3□PbTiO3 thin films. *Thin Solid Films*, **2003**, 424, 274-282	2.2	28
152	Normal ferroelectric to relaxor behavior in laser ablated Ca-doped barium titanate thin films. *Journal of Applied Physics*, **2003**, 94, 7702	2.5	90
151	Growth and electrical characterization of laser ablated highly oriented zirconium titanate thin films in a metal□oxide semiconductor configuration. *Semiconductor Science and Technology*, **2003**, 18, 183-189	1.8	12

150	Interface states of laser ablated BaTiO3 and Ba0.9Ca0.1TiO3 thin films in MFS structure determined by DLTS and C V technique. *Materials Research Society Symposia Proceedings*, **2003**, 784, 3111		
149	Growth and Studies of Calcium Doped Laser Ablated Barium Titanate Thin Films. *Integrated Ferroelectrics*, **2003**, 54, 747-754	0.8	
148	Dielectric properties of La-modified antiferroelectric PbZrO3 thin films. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2002**, 88, 22-25	3.1	12
147	Reversible and irreversible switching processes in pure and lanthanum modified lead zirconate thin films. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2002**, 94, 218-222	3.1	5
146	Electrical characterization of Ba(Zr0.1Ti0.9)O3 thin films grown by pulsed laser ablation technique. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2002**, 95, 124-130	3.1	15
145	Investigation of reversible and irreversible polarizations in thin films of SrBi2(Ta0.5,Nb0.5)2O9. *Thin Solid Films*, **2002**, 422, 155-160	2.2	15
144	Pulsed excimer laser ablation growth and characterization of Ba(Sn0.1Ti0.9)O3 thin films. *Solid State Communications*, **2002**, 121, 329-332	1.6	23
143	Growth and characterization of Ba(Zr0.1Ti0.9)O3 thin films deposited by pulsed excimer laser ablation. *Solid State Communications*, **2002**, 122, 429-432	1.6	6
142	Dielectric and ferroelectric response of sol gel derived Pb0.85La0.15TiO3 ferroelectric thin films on different bottom electrodes. *Thin Solid Films*, **2002**, 406, 30-39	2.2	10
141	Analysis of leakage current conduction phenomenon in thin SrBi2Ta2O9 films grown by excimer laser ablation. *Journal of Applied Physics*, **2002**, 91, 4543-4548	2.5	27
140	Impact of Sr content on dielectric and electrical properties of pulsed laser ablated SrBi2Ta2O9 thin films. *Journal of Applied Physics*, **2002**, 92, 1056-1061	2.5	7
139	ac transport studies of La-modified antiferroelectric lead zirconate thin films. *Physical Review B*, **2002**, 65,	3.3	27
138	Leakage current conduction of pulsed excimer laser ablated BaBi2Nb2O9 thin films. *Journal of Applied Physics*, **2002**, 92, 415-420	2.5	22
137	Alternating Current Conduction and Impedance Spectroscopy Analysis on Pulsed Excimer Laser Ablated (Pb, La)TiO 3 Thin Films. *Integrated Ferroelectrics*, **2002**, 46, 143-152	0.8	2
136	The Thickness Dependence of the Electrical and Dielectric Properties in the Laser Ablated SrBi 2 Nb 2 O 9 Thin Films. *Integrated Ferroelectrics*, **2002**, 50, 159-169	0.8	
135	Dielectric Properties of Pulsed Excimer Laser Ablated BaBi2Nb2O9 Thin Films. *Materials Research Society Symposia Proceedings*, **2002**, 748, 1		
134	MFIS and MFS structures using SrBi2Ta2O9 thin films for the FRAM applications. *Materials Research Society Symposia Proceedings*, **2002**, 747, 1		
133	MFIS and MFS structures using SrBi2Ta2O9 thin films for the FRAM applications. *Materials Research Society Symposia Proceedings*, **2002**, 748, 1		

132	Study of Relaxor Behavior of 0.7Pb(Mg 1/3 Nb 2/3)O 3 -0.3PbTiO 3 Thin Films. *Integrated Ferroelectrics*, **2002**, 46, 153-162	0.8	1
131	Study of Thickness Dependence on Electrical Properties of (Pb,La)TiO 3 Thin Films for Memory Applications. *Integrated Ferroelectrics*, **2002**, 46, 133-141	0.8	1
130	Study of layered structured ferroelectric materials grown by laser ablation. *Ferroelectrics*, **2001**, 260, 161-167	0.6	
129	Antiferroelectric thin films for MEMs applications. *Ferroelectrics*, **2001**, 263, 39-44	0.6	12
128	Dielectric response and complex impedance spectroscopy studies in pulsed laser ablated (Ba, Sr)TiO3 thin films. *Integrated Ferroelectrics*, **2001**, 33, 331-342	0.8	5
127	Laser ablation and characterization of cabi2ta2o9 thin films. *Integrated Ferroelectrics*, **2001**, 36, 63-71	0.8	1
126	Study of pulsed laser deposited lead lanthanum titanate thin films. *Thin Solid Films*, **2001**, 389, 84-90	2.2	13
125	Study of AC electrical properties in multigrain antiferroelectric lead zirconate thin films. *Thin Solid Films*, **2001**, 391, 126-132	2.2	15
124	Study of pulsed laser ablated CaBi2Ta2O9 thin films. *Solid State Communications*, **2001**, 119, 127-131	1.6	5
123	Temperature dependence on the response of inversion layer with zirconium titanate as oxide in MOS configuration. *Solid State Communications*, **2001**, 120, 379-382	1.6	9
122	Electrical transport characteristics of Au/n-GaAs Schottky diodes on n-Ge at low temperatures. *Solid-State Electronics*, **2001**, 45, 133-141	1.7	142
121	Doping dependence of the barrier height and ideality factor of Au/n-GaAs Schottky diodes at low temperatures. *Physica B: Condensed Matter*, **2001**, 307, 125-137	2.8	102
120	Electrical properties of La-graded heterostructure of Pb1−LaxTiO3 thin films. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2001**, 86, 172-177	3.1	9
119	Interface states density distribution in Au/n-GaAs Schottky diodes on n-Ge and n-GaAs substrates. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2001**, 87, 141-147	3.1	84
118	AC and DC conductivity studies in pulsed laser ablated (Ba, Sr)TiO3 thin films. *Integrated Ferroelectrics*, **2001**, 33, 353-361	0.8	3
117	Antiferroelectric lead zirconate thin films by excimer laser ablation. *Integrated Ferroelectrics*, **2001**, 35, 249-259	0.8	
116	Ferroelectric thin films: Preparation and characterization. *Thin Films*, **2001**, 375-434		1
115	Effect of acceptor and donor dopants on polarization components of lead zirconate titanate thin films. *Applied Physics Letters*, **2001**, 79, 239-241	3.4	33

114	Large reduction of leakage current by graded-layer La doping in (Ba0.5, Sr0.5)TiO3 thin films. *Applied Physics Letters*, **2001**, 79, 111-113	3.4	35
113	Transient analysis in Al-doped barium strontium titanate thin films grown by pulsed laser deposition. *Journal of Applied Physics*, **2001**, 90, 1250-1254	2.5	11
112	Self-annihilation of antiphase boundaries in GaAs epilayers on Ge substrates grown by metal-organic vapor-phase epitaxy. *Journal of Applied Physics*, **2001**, 89, 5972-5979	2.5	36
111	Improvement of the degradation characteristics of sol-gel derived PZT (53/47) thin films : Effect of conventional and graded iron doping. *Integrated Ferroelectrics*, **2001**, 39, 127-136	0.8	8
110	CaBi2Ta2O9 ferroelectric thin films prepared by pulsed laser deposition. *Applied Physics Letters*, **2001**, 78, 2925-2927	3.4	13
109	AC electrical property studies on SrBi2(Ta0.5,Nb0.5)2O9 thin films by excimer laser ablation. *Integrated Ferroelectrics*, **2001**, 32, 101-119	0.8	1
108	Micro-Raman and dielectric phase transition studies in antiferroelectric PbZrO3 thin films. *Applied Physics Letters*, **2001**, 78, 1730-1732	3.4	18
107	Structural and electrical characteristics of Pb0.90La0.15TiO3 thin films on different bottom electrodes. *Journal of Applied Physics*, **2001**, 89, 5637-5643	2.5	18
106	Backward switching phenomenon from field forced ferroelectric to antiferroelectric phases in antiferroelectric PbZrO3 thin films. *Journal of Applied Physics*, **2001**, 89, 4541-4547	2.5	46
105	Effect of neodymium (Nd) doping on the dielectric and ferroelectric characteristics of sol-gel derived lead zirconate titanate (53/47) thin films. *Journal of Applied Physics*, **2001**, 90, 2975-2984	2.5	60
104	Analysis of Alternating Current Conduction and Impedance Spectroscopy Study of BaBi2Nb2O9 Thin Films. *Materials Research Society Symposia Proceedings*, **2001**, 688, 1		
103	Impact of Template Layers on Dielectric and Electrical Properties of Pulsed-Laser Ablated Pb(Mg1/3 Nb2/3)O3 - PbTiO3 Thin Films. *Materials Research Society Symposia Proceedings*, **2001**, 688, 1		
102	Growth and study of SrBi2 (Ta, Nb)2 O9 thin films by pulsed excimer laser ablation. *Solid State Communications*, **2000**, 114, 585-588	1.6	9
101	Pulsed excimer laser ablated copper indium diselenide thin films. *Solid State Communications*, **2000**, 116, 649-653	1.6	18
100	Effects of thin oxide in metal□emiconductor and metal□nsulator□emiconductor epi-GaAs Schottky diodes. *Solid-State Electronics*, **2000**, 44, 1089-1097	1.7	131
99	Dielectric and dc electrical studies of antiferroelectric lead zirconate thin films. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2000**, 78, 1-10	3.1	9
98	Dielectric relaxation in antiferroelectric multigrain PbZrO3 thin films. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2000**, 78, 75-83	3.1	26
97	Transmission electron microscopic study of GaAs/Ge heterostructures grown by low-pressure metal organic vapor phase epitaxy. *Materials Research Bulletin*, **2000**, 35, 125-133	5.1	11

96	Atomic force microscopic study of surface morphology in Si-doped epi-GaAs on Ge substrates: effect of off-orientation. *Materials Research Bulletin*, **2000**, 35, 909-919	5.1	22
95	Excimer laser ablation processed ferroelectric and antiferroelectric thin films. *Integrated Ferroelectrics*, **2000**, 31, 1-12	0.8	
94	Alternating current electrical properties of antiferroelectric lead zirconate thin films by pulsed excimer laser ablation. *Journal of Applied Physics*, **2000**, 88, 2072-2080	2.5	17
93	Growth and characterization of excimer laser-ablated BaBi2Nb2O9 thin films. *Applied Physics Letters*, **2000**, 77, 3818-3820	3.4	21
92	Microstructure related influence on the electrical properties of pulsed laser ablated (Ba, Sr)TiO3 thin films. *Journal of Applied Physics*, **2000**, 88, 3506-3513	2.5	35
91	Alternating current conduction behavior of excimer laser ablated SrBi[sub 2]Nb[sub 2]O[sub 9] thin films. *Journal of Applied Physics*, **2000**, 88, 4294	2.5	46
90	Field-induced dielectric properties of laser ablated antiferroelectric (Pb0.99Nb0.02)(Zr0.57Sn0.38Ti0.05)0.98O3 thin films. *Applied Physics Letters*, **2000**, 77, 4208-4210	3.4	4
89	Impact of microstructure on the electrical stress induced effects of pulsed laser ablated (Ba, Sr)TiO3 thin films. *Journal of Applied Physics*, **2000**, 87, 3056-3062	2.5	29
88	Dielectric response in pulsed laser ablated (Ba,Sr)TiO3 thin films. *Journal of Applied Physics*, **2000**, 87, 849-854	2.5	62
87	Growth and characterization of SrBi2Nb2O9 thin films by pulsed-laser ablation. *Applied Physics Letters*, **1999**, 75, 2656-2658	3.4	29
86	Breakdown characteristics of MOVPE grown Si-doped GaAs Schottky diodes. *Solid-State Electronics*, **1999**, 43, 2135-2139	1.7	3
85	Study of the electrical properties of pulsed laser ablated (Ba0.5Sr0.5)TiO3 thin films. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **1999**, 57, 135-146	3.1	46
84	Si incorporation and Burstein□Moss shift in n-type GaAs. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **1999**, 60, 1-11	3.1	30
83	Impedance-fatigue correlated studies on SrBi2Ta2O9. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **1999**, 64, 149-156	3.1	32
82	Antiferroelectric lead zirconate thin films by pulsed laser ablation. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **1999**, 64, 54-59	3.1	12
81	Anomalous current transport in Au/low-doped n-GaAs Schottky barrier diodes at low temperatures. *Applied Physics A: Materials Science and Processing*, **1999**, 68, 49-55	2.6	67
80	Growth, optical, and electron transport studies across isotype n-GaAs/n-Ge heterojunctions. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **1999**, 17, 1003		16
79	Growth and study of antiferroelectric lead zirconate thin films by pulsed laser ablation. *Journal of Applied Physics*, **1999**, 86, 5862-5869	2.5	72

78	OMVPE growth of undoped and Si-doped GaAs epitaxial layers on Ge. *Journal of Crystal Growth*, **1998**, 193, 501-509	1.6	13
77	Correlation of compensation in Si-doped GaAs between electrical and optical methods. *Solid State Communications*, **1998**, 108, 457-461	1.6	4
76	Role of growth conditions and Bi-content on the properties of SrBi2Ta2O9 thin films. *Solid State Communications*, **1998**, 108, 759-763	1.6	6
75	Comparative studies of Si-doped n-type MOVPE GaAs on Ge and GaAs substrates. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **1998**, 55, 53-67	3.1	14
74	Low temperature photoluminescence properties of Zn-doped GaAs. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **1998**, 57, 62-70	3.1	13
73	Photoluminescence studies on Si-doped GaAs/Ge. *Journal of Applied Physics*, **1998**, 83, 4454-4461	2.5	23
72	Zn incorporation and band gap shrinkage in p-type GaAs. *Journal of Applied Physics*, **1997**, 82, 4931-4937	2.5	29
71	Electron cyclotron resonance plasma assisted sputter deposition of boron nitride films. *Applied Physics Letters*, **1997**, 70, 628-630	3.4	8
70	Studies on structural and electrical properties of barium strontium titanate thin films developed by metallo-organic decomposition. *Thin Solid Films*, **1997**, 305, 144-156	2.2	61
69	Effect of VIII ratio on the optical properties of MOCVD grown undoped GaAs layers. *Solid State Communications*, **1997**, 103, 411-416	1.6	6
68	Growth and Characterization of GaAs Epitaxial Layers by MOCVD. *Materials Research Society Symposia Proceedings*, **1996**, 421, 281		2
67	Sputter Synthesis of Ferroelectric Films and Heterostructures. *MRS Bulletin*, **1996**, 21, 25-30	3.2	32
66	Rapid thermal processed thin films of niobium pentoxide (Nb2 O5) deposited by reactive magnetron sputtering. *Thin Solid Films*, **1995**, 261, 18-24	2.2	4
65	Rapid thermal processed thin films of reactively sputtered Ta2O5. *Thin Solid Films*, **1995**, 258, 230-235	2.2	88
64	Reactive magnetron co-sputtered antiferroelectric lead zirconate thin films. *Applied Physics Letters*, **1995**, 67, 2014-2016	3.4	87
63	Structures and electrical properties of barium strontium titanate thin films grown by multi-ion-beam reactive sputtering technique. *Journal of Materials Research*, **1995**, 10, 708-726	2.5	96
62	Pt/Ti/SiO2/Si substrates. *Journal of Materials Research*, **1995**, 10, 1508-1515	2.5	84
61	Thickness-dependent electrical characteristics of lead zirconate titanate thin films. *Journal of Applied Physics*, **1995**, 77, 3981-3986	2.5	114

60	Low Energy Ion Bombardment Induced Effects in Multicomponent Electroceramic Thin Films **1995**, 23-51		2
59	Dependence of perovskite/pyrochlore phase formation on oxygen stoichiometry in PLT thin films. *Journal of Materials Research*, **1994**, 9, 699-711	2.5	43
58	Study of electrical properties of pulsed excimer laser deposited strontium titanate films. *Journal of Applied Physics*, **1994**, 75, 2604-2611	2.5	32
57	Pulsed excimer laser ablation of (Pb,La)TiO3 thin films for dynamic random access memory devices. *Applied Physics Letters*, **1994**, 64, 1591-1593	3.4	30
56	Pulsed laser deposition of strontium titanate thin films for dynamic random access memory applications. *Thin Solid Films*, **1994**, 249, 100-108	2.2	7
55	Current-voltage characteristics of ultrafine-grained ferroelectric Pb(Zr, Ti)O3 thin films. *Journal of Materials Research*, **1994**, 9, 1484-1498	2.5	141
54	Process-property correlations of excimer laser ablated bismuth titanate films on silicon. *Journal of Applied Physics*, **1993**, 74, 7551-7560	2.5	12
53	Structural and electrical characteristics of SrTiO3 thin films for dynamic random access memory applications. *Journal of Applied Physics*, **1993**, 73, 7627-7634	2.5	177
52	Electrical properties of strontium titanate thin films by multi-ion-beam reactive sputtering technique. *Applied Physics Letters*, **1993**, 63, 1038-1040	3.4	32
51	Composition/structure/property relations of multi-ion-beam reactive sputtered lead lanthanum titanate thin films: Part III. Electrical properties. *Journal of Materials Research*, **1993**, 8, 2203-2215	2.5	17
50	Low-energy oxygen ion bombardment effect on BaTiO3 thin films grown by multi-ion-beam reactive sputtering technique. *Applied Physics Letters*, **1993**, 63, 734-736	3.4	7
49	Switching, fatigue, and retention in ferroelectric Bi4Ti3O12 thin films. *Applied Physics Letters*, **1993**, 62, 1928-1930	3.4	131
48	Electron-cyclotron-resonance plasma-assisted radio-frequency-sputtered strontium titanate thin films. *Journal of Applied Physics*, **1993**, 74, 6851-6858	2.5	16
47	Nonlinear electrical properties of lead-lanthanum-titanate thin films deposited by multi-ion-beam reactive sputtering. *Journal of Applied Physics*, **1993**, 74, 1949-1959	2.5	62
46	Enhanced electrical properties of ferroelectric Pb(Zr0.5, Ti0.5)O3 thin films grown with low-energy oxygen ion assistance. *Journal of Applied Physics*, **1993**, 74, 3373-3382	2.5	31
45	Switching characteristics of multi-ion-beam reactive sputter deposited Pb(Zr,Ti)O3 thin films. *Applied Physics Letters*, **1993**, 62, 651-653	3.4	4
44	Excimer laser ablated barium strontium titanate thin films for dynamic random access memory applications. *Applied Physics Letters*, **1993**, 62, 1056-1058	3.4	131
43	Composition/structure/property relations of multi-ion-beam reactive sputtered lead lanthanum titanate thin films: Part II. Textured microstructure development. *Journal of Materials Research*, **1993**, 8, 2191-2202	2.5	12

42	Spectroscopic ellipsometry studies on ion beam sputter deposited Pb(Zr, Ti)O3 films on sapphire and Pt-coated silicon substrates. *Thin Solid Films*, **1993**, 230, 15-27	2.2	41
41	Effect of heating rate on the crystallization behavior of amorphous PZT thin films. *Thin Solid Films*, **1993**, 223, 327-333	2.2	75
40	Origin of Orientation in Sol-Gel-Derived Lead Titanate Films. *Journal of the American Ceramic Society*, **1993**, 76, 1345-1348	3.8	60
39	Ferroelectric Thin Films and Device Applications **1993**, 601-625		0
38	Electrical characteristics of excimer laser ablated bismuth titanate films on silicon. *Journal of Applied Physics*, **1992**, 72, 3617-3621	2.5	52
37	Pulsed excimer laser deposition of ferroelectric thin films. *Integrated Ferroelectrics*, **1992**, 1, 253-268	0.8	12
36	Excimer laser ablated strontium titanate thin films for dynamic random access memory applications. *Applied Physics Letters*, **1992**, 60, 2478-2480	3.4	50
35	Effect of low pressure dc plasma discharge on laser ablated ferroelectric Pb(Zr,Ti)O3 thin films. *Journal of Applied Physics*, **1992**, 72, 620-625	2.5	13
34	Strontium titanate thin films by rapid thermal processing. *Applied Physics Letters*, **1992**, 61, 1525-1527	3.4	47
33	Growth of ferroelectric oxide thin films by excimer laser ablation. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **1992**, 10, 1815-1820	2.9	11
32	Pulsed excimer laser ablated barium titanate thin films. *Applied Physics Letters*, **1992**, 61, 2057-2059	3.4	78
31	Property modification of ferroelectric Pb(Zr,Ti)O3 thin films by low-energy oxygen ion bombardment during film growth. *Applied Physics Letters*, **1992**, 61, 1246-1248	3.4	26
30	Rapid thermally processed ferroelectric Bi4Ti3O12 thin films. *Journal of Applied Physics*, **1992**, 72, 5517-5519	2.5	75
29	Polarization reversal and high dielectric permittivity in lead magnesium niobate titanate thin films. *Applied Physics Letters*, **1992**, 60, 1187-1189	3.4	54
28	Multi-ion-beam reactive sputter deposition of ferroelectric Pb(Zr,Ti)O3 thin films. *Journal of Applied Physics*, **1992**, 71, 376-388	2.5	111
27	Oriented lead germanate thin films by excimer laser ablation. *Applied Physics Letters*, **1992**, 60, 827-829	3.4	11
26	Recent advances in physical vapor growth processes for ferroelectric thin films. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **1992**, 10, 1569-1577	2.9	26
25	Recent advances in the deposition of ferroelectric thin films. *Integrated Ferroelectrics*, **1992**, 1, 161-180	0.8	5

24	Composition/structure/property relations of multi-ion-beam reactive sputtered lead lanthanum titanate thin films: Part I. Composition and structure analysis. *Journal of Materials Research*, **1992**, 7, 3039-3055	2.5	40
23	Pulsed excimer laser deposition and characterization of ferroelectric Pb(Zr0.52Ti0.48)O3 thin films. *Journal of Materials Research*, **1992**, 7, 2521-2529	2.5	31
22	Development of ferroelectric Pb(ZrxTi1)O3 thin films by metallo-organic decomposition process and rapid thermal annealing. *Integrated Ferroelectrics*, **1992**, 1, 111-127	0.8	31
21	Excimer laser-ablated bismuth titanate thin films. *Applied Physics Letters*, **1992**, 60, 781-783	3.4	42
20	Structural and electrical studies on rapid thermally processed ferroelectric Bi4Ti3O12 thin films by metallo-organic solution deposition. *Journal of Applied Physics*, **1992**, 72, 5827-5833	2.5	101
19	Excimer laser ablation of ferroelectric Pb(Zr,Ti)O3 thin films with low pressure direct-current glow discharge. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **1992**, 10, 1827-1831	2.9	19
18	Excimer laser ablated deposition of ferroelectric lead germanate thin films. *Thin Solid Films*, **1992**, 219, 162-169	2.2	6
17	Excimer laser ablated lead zirconate titanate thin films. *Journal of Applied Physics*, **1991**, 69, 7930-7932	2.5	66
16	Studies of MZS and MZOS Structures with Zinc Oxide Deposited by Conventional Rf Diode and Magnetron Sputtering Techniques. *Materials Research Society Symposia Proceedings*, **1986**, 77, 289		1
15	Rf Magnetron Sputter Deposition and Characterization of Aluminum Nitride thin Films. *Materials Research Society Symposia Proceedings*, **1986**, 77, 399		3
14	Position and pressure effects in rf magnetron reactive sputter deposition of piezoelectric zinc oxide. *Journal of Applied Physics*, **1984**, 56, 3308-3318	2.5	96
13	Radio frequency magnetron sputtering of multicomponent ferroelectric oxides. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **1984**, 2, 303-306	2.9	12
12	Electrical characterization of amorphous germanium dioxide films. *Thin Solid Films*, **1984**, 113, 173-184	2.2	10
11	I-V & C-V characteristics of ferroelectric lead germanate on silicon. *Ferroelectrics*, **1983**, 50, 117-122	0.6	5
10	rf planar magnetron sputtering and characterization of ferroelectric Pb(Zr,Ti)O3 films. *Journal of Applied Physics*, **1983**, 54, 6601-6609	2.5	192
9	I-V and C-V studies of evaporated amorphous arsenic telluride film on crystalline silicon. *Journal of Applied Physics*, **1983**, 54, 1383-1389	2.5	5
8	R.F. magnetron sputtering of ferroelectric PZT films. *Ferroelectrics*, **1983**, 51, 93-98	0.6	5
7	Ferroelectric field effect in Te on TGSe substrate. *Solid-State Electronics*, **1981**, 24, 91-95	1.7	1

6	A study of the ferroelectric field effect in Te films on lead germanate, triglycine sulphate, and triglycine selenate substrates. *Journal of Applied Physics*, **1981**, 52, 5274-5282	2.5	6
5	Electrical switching in single crystal VO2. *Solid-State Electronics*, **1980**, 23, 649-654	1.7	16
4	Preparation and properties of thermally evaporated lead germanate films. *Journal of Applied Physics*, **1980**, 51, 5408	2.5	28
3	Low frequency electrical behavior of ferroelectric MASD. *Journal of Chemical Physics*, **1978**, 69, 3039-3043	3.9	0
2	Impact of microstructure on the electrical properties of zirconium titanate thin films in MOS configuration		1
1	Pulsed Laser Deposition of Transition Metal Dichalcogenides-Based Heterostructures for Efficient Photodetection		1